TOSHIBA Field Effect Transistor Silicon N Channel MOS Type  $(\pi - MOSVII)$ 

# TK4A60D

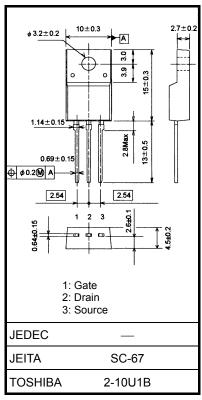
## **Switching Regulator Applications**

Unit: mm

- Low drain-source ON-resistance: RDS (ON) =  $1.4 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.5 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 600 \text{ V)}$
- Enhancement mode:  $V_{th} = 2.4 \text{ to } 4.4 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteristics                      |                       | Symbol           | Rating     | Unit |
|--------------------------------------|-----------------------|------------------|------------|------|
| Drain-source voltage                 |                       | $V_{DSS}$        | 600        | V    |
| Gate-source voltage                  |                       | $V_{GSS}$        | ±30        | V    |
| Drain current                        | DC (Note 1)           | I <sub>D</sub>   | 4          | Α    |
|                                      | Pulse (Note 1)        | I <sub>DP</sub>  | 16         | A    |
| Drain power dissipation              | on (Tc = 25°C)        | P <sub>D</sub>   | 35         | W    |
| Single pulse avalanch                | ne energy<br>(Note 2) | E <sub>AS</sub>  | 187        | mJ   |
| Avalanche current                    |                       | I <sub>AR</sub>  | 4          | Α    |
| Repetitive avalanche energy (Note 3) |                       | E <sub>AR</sub>  | 3.5        | mJ   |
| Channel temperature                  |                       | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature range            |                       | T <sub>stg</sub> | -55 to 150 | °C   |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 3.57 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

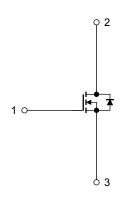
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 20.5 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 4 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Internal Connection



Start of commercial production 2008-10

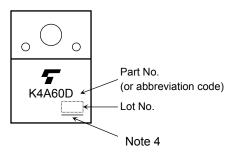
## **Electrical Characteristics (Ta = 25°C)**

| Chara                        | acteristics    | Symbol               | Test Condition   | Min | Тур. | Max | Unit |
|------------------------------|----------------|----------------------|--|-----|------|-----|------|
| Gate leakage cur             | rent           | I <sub>GSS</sub>     | $V_{GS}=\pm30~V,~V_{DS}=0~V$   | _   | _    | ±1  | μΑ   |
| Drain cut-off current        |                | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V   | _   | _    | 10  | μΑ   |
| Drain-source brea            | akdown voltage | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$  | 600 | _    | _   | V    |
| Gate threshold vo            | oltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 2.4 | _    | 4.4 | V    |
| Drain-source ON              | -resistance    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A   | _   | 1.4  | 1.7 | Ω    |
| Forward transfer             | admittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2 A   | 0.7 | 2.5  | _   | S    |
| Input capacitance            |                | C <sub>iss</sub>     |  | _   | 600  | _   | pF   |
| Reverse transfer capacitance |                | C <sub>rss</sub>     | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$   | _   | 4    | _   |      |
| Output capacitance           |                | Coss                 |  | _   | 70   | _   |      |
| Switching time               | Rise time      | t <sub>r</sub>       | $\begin{array}{c c} 10 \text{ V} \\ V_{GS} \\ 0 \text{ V} \\ \hline \\ 50 \Omega \end{array}$ $\begin{array}{c c} I_D = 2 \text{ A} & V_{OUT} \\ \hline \\ R_L = 100 \Omega \\ \hline \\ V_{DD} \approx 200 \text{ V} \end{array}$ | _   | 18   | _   | . ns |
|                              | Turn-on time   | t <sub>on</sub>      |  | _   | 40   | _   |      |
|                              | Fall time      | t <sub>f</sub>       |  | _   | 8    | _   |      |
|                              | Turn-off time  | t <sub>off</sub>     | Duty $\leq$ 1%, $t_W = 10 \mu s$   | _   | 55   | _   |      |
| Total gate charge            |                | Qg                   |  | _   | 12   | _   |      |
| Gate-source charge           |                | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$   | _   | 7    | _   | nC   |
| Gate-drain charge            |                | Q <sub>gd</sub>      |  | _   | 5    | _   |      |

# **Source-Drain Ratings and Characteristics (Ta = 25°C)**

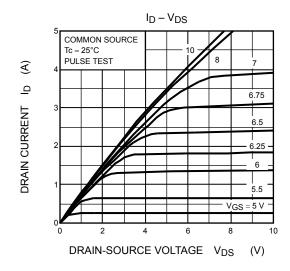
| Characteristics                           | Symbol           | Test Condition                               | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _  | _   | _    | 4    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _  | _   | _    | 16   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 4 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | $I_{DR} = 4 A$ , $V_{GS} = 0 V$ ,            | _   | 1200 | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> /dt = 100 A/μs              | _   | 7    | _    | μС   |

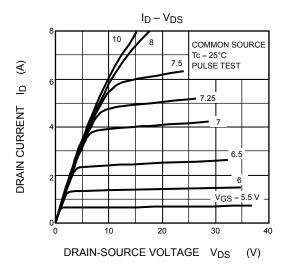
## **Marking**

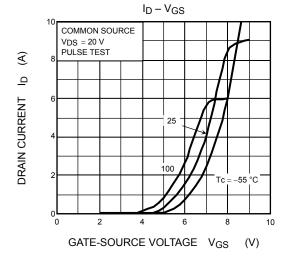


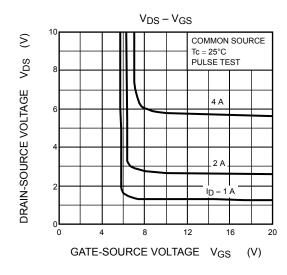
Note 4: A line under a Lot No. identifies the indication of product Labels. [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

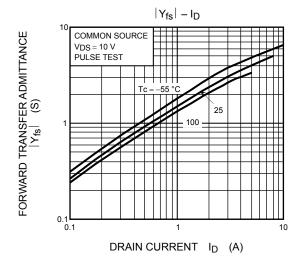
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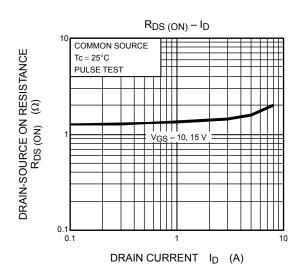




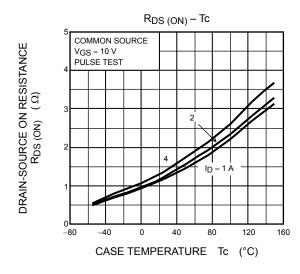


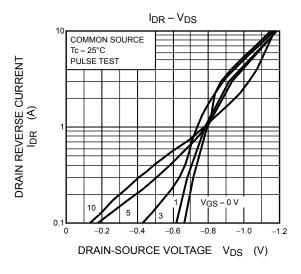


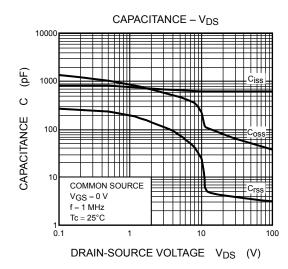


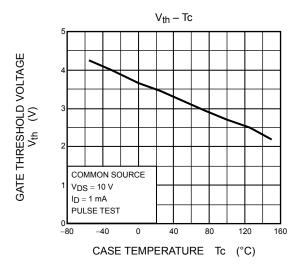


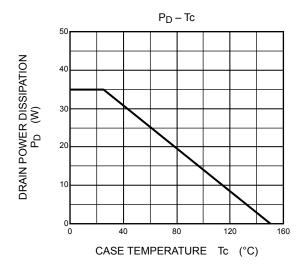
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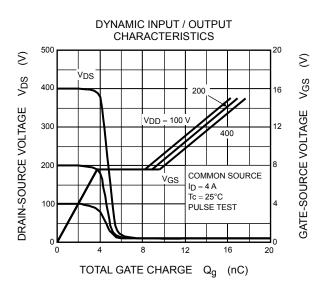


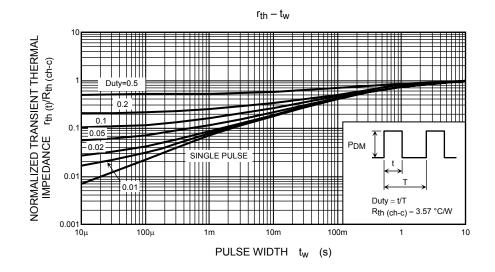


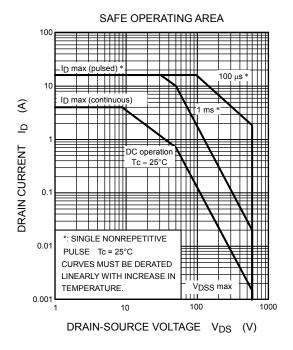


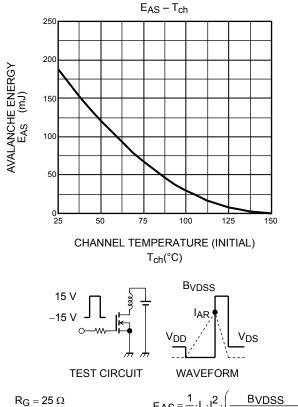












$$\begin{aligned} &R_G = 25~\Omega\\ &V_{DD} = 90~V,~L = 20.5~mH \end{aligned} \qquad \text{EAS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{\text{BVDSS}}{\text{BVDSS} - \text{VDD}} \right)$$

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